



PRODUCT NAME : 2N3553 NPN VHF-UHF T
ransistor (Pack of 5)

PRICE : Rs 20.00

SKU : RM2016



DESCRIPTION

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Features

- Collector-Emitter Volt (V_{ce0}): 40V
- Collector-Base Volt (V_{cb0}): 65V
- Collector Current (I_c): 1.0A
- h_{fe} : 15-200 @ 125mA
- Power Dissipation (P_{tot}): 7000mW
- Current-Gain-Bandwidth (f_{total}): 500MHz
- Type: NPN

Silicon planar epitaxial overlay transistor

2N3553

APPLICATIONS

- The 2N3553 is intended for use in VHF and UHF transmitting applications.

DESCRIPTION

The device is a silicon NPN overlay transistor in a TO-39 metal package with the collector connected to the case.

PINNING - TO-39/3

PIN	DESCRIPTION
1	emitter
2	base
3	collector

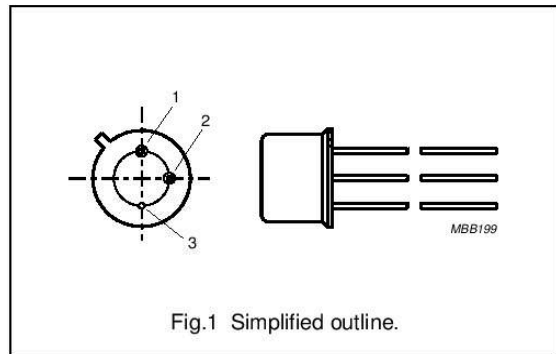


Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_{CEX}	collector-emitter voltage	$I_C \leq 200 \text{ mA}$; $V_{BE} = -1.5 \text{ V}$	65	V
V_{CEO}	collector-emitter voltage	open base; $I_C \leq 200 \text{ mA}$	40	V
I_{CM}	peak collector current		1.0	A
P_{tot}	total power dissipation	up to $T_{mb} = 25 \text{ }^\circ\text{C}$	7.0	W
T_j	junction temperature		200	$^\circ\text{C}$
f_T	transition frequency	$I_C = 125 \text{ mA}$; $V_{CE} = 28 \text{ V}$	500	–

RF performance

f (MHz)	V_{CE} (V)	P_o (W)	G_p (dB)	η (%)
175	28	2.5	>10	>50

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

**Silicon planar epitaxial
 overlay transistor**

2N3553

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	65	V
V_{CEX}	collector-emitter voltage	$I_C \leq 200$ mA; $V_{BE} = -1.5$ V	–	65	V
V_{CEO}	collector-emitter voltage	open base; $I_C \leq 200$ mA	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	4	V
I_C	collector current (DC)		–	0.35	A
I_{CM}	peak collector current		–	1	A
P_{tot}	total power dissipation	up to $T_{mb} = 25$ °C	–	7	W
T_{stg}	storage temperature		–65	+200	°C
T_j	junction temperature		–	200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	25	K/W

